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# 40Mbps, +3.3V, RS-485 Half-Duplex Transceivers

### **General Description**

### **Features**

- Half-Duplex RS-485 Transceivers
- +3.3V Supply Voltage
- ♦ 40Mbps Maximum Data Rate
- Large (170mV) Receiver Hysteresis on MAX14840E
- Symmetrical Fail-Safe Receiver Input on MAX14840E
- Fail-Safe Receiver Input (MAX14841E)
- Hot-Swap Capability
- Short-Circuit Protected Outputs
- Thermal Self-Protection
- Low 10µA (max) Shutdown Current
- Extended ESD Protection for RS-485 I/O Pins ±35kV Human Body Model (HBM)
  ±20kV Air-Gap Discharge per IEC 61000-4-2
  ±12kV Contact Discharge per IEC 61000-4-2
- Automotive -40°C to +125°C Operating Temperature Range
- Available in Industry-Standard 8-Pin SO or Space-Saving, 8-Pin TDFN-EP (3mm x 3mm) Packages

cation up to 40Mbps. These transceivers are optimized for high speeds over extended cable runs while minimizing tolerance to noise. The MAX14840E features symmetrical fail-safe and larger receiver hysteresis, providing improved noise rejec-

The MAX14840E/MAX14841E are +3.3V ESD-protected

transceivers intended for half-duplex RS-485 communi-

er receiver hysteresis, providing improved noise rejection and improved recovered signals in high-speed and long cable applications. The MAX14841E has true failsafe receiver inputs guaranteeing a logic-high receiver output when inputs are shorted or open.

The MAX14840E/MAX14841E transceivers draw 1.5mA (typ) supply current when unloaded or when fully loaded with the drivers disabled. Hot-swap capability eliminates undesired transitions on the bus during power-up or hot insertion.

The MAX14840E/MAX14841E are available in 8-pin SO and small, 8-pin ( $3mm \times 3mm$ ) TDFN-EP packages. Both devices operate over the -40°C to +125°C automotive temperature range.

### **Applications**

Motion Controllers Fieldbus Networks Industrial Control Systems Backplane Buses HVAC Networks

### **Ordering Information/Selector Guide**

PART	FAIL SAFE	TEMP RANGE	PIN-PACKAGE
MAX14840EASA+	MAX14840EASA+ Symmetrical		8 SO
MAX14840EATA+	Symmetrical	-40°C to +125°C	8 TDFN-EP*
MAX14841EASA+	True	-40°C to +125°C	8 SO
MAX14841EATA+	True	-40°C to +125°C	8 TDFN-EP*

+Denotes a lead(Pb)-free/RoHS-compliant package.

\*EP = Exposed pad.

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For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

### **ABSOLUTE MAXIMUM RATINGS**

(Voltages referenced to GND.)

VCC -0.3V to +6.0V
RE, RO0.3V to +(V <sub>CC</sub> + 0.3V)
DE, DI0.3V to +6.0V
A, B8.0V to +13.0V
Short-Circuit Duration (RO, A, B) to GND Continuous
Continuous Power Dissipation ( $T_A = +70^{\circ}C$ )
8-Pin SO (derate 7.6mW/°C above +70°C) 606mW
8-Pin TDFN (derate 24.4mW/°C above +70°C) 1951mW
Junction-to-Case Thermal Resistance ( $\theta_{JC}$ ) (Note 1)
8-Pin SO
8-Pin TDFN

Junction-to-Ambient Thermal Resistance ( $\theta_{JA}$ ) (Note 1)						
8-Pin SO	132°C/W					
8-Pin TDFN	41°C/W					
Operating Temperature Range	-40°C to +125°C					
Junction Temperature	+150°C					
Storage Temperature Range	-65°C to +150°C					
Lead Temperature (soldering, 10s)	+300°C					
Soldering Temperature (reflow)	+260°C					

**Note 1:** Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a fourlayer board. For detailed information on package thermal considerations, refer to <u>www.maxim-ic.com/thermal-tutorial</u>.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS

(VCC = +3.0V to +3.6V, TA = -40°C to +125°C, unless otherwise noted. Typical values are at VCC = +3.3V and TA = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS
POWER SUPPLY							
Supply Voltage	Vcc			3.0		3.6	V
Supply Current	ICC	$\begin{array}{l} DE = \overline{RE} = V_{CC},  or \\ DE = \overline{RE} = GND,  or \\ DE = V_{CC},  \overline{RE} = GND, \\ DI = V_{CC}  or  GND,  no  load \end{array}$			1.5	4	mA
Shutdown Supply Current	ISH	$DE = GND$ and $\overline{RE} = VCC$	;			10	μA
DRIVER							
Differential Driver Output	Vod	$R_L = 54\Omega$ , Figure 1		1.5			V
Change in Magnitude of Differential Output Voltage	ΔVod	$R_L = 54\Omega$ , Figure 1 (Note 4)		-0.2	0	+0.2	V
Driver Common-Mode Output Voltage	Voc	$R_L = 54\Omega$ , Figure 1			Vcc/2	3	V
Change in Common-Mode Voltage	ΔVoc	$R_L = 54\Omega$ , Figure 1 (Note 4)		-0.2		0.2	V
Single-Ended Driver Output High	Voh	A/B output, IOUT = -20mA	N N	2.2			V
Single-Ended Driver Output Low	Vol	A/B output, IOUT = 20mA				0.8	V
Driver Short-Circuit Output	0V ≤ VOL					250	mA
Current	llosdi			250			
RECEIVER							
Input Current (A and B)	I <sub>A,B</sub>	DE = GND,	$V_{IN} = +12V$			1000	μA
	чА,В	$V_{CC} = GND \text{ or } +3.6V$	$V_{IN} = -7V$	-800			μΑ
Differential Input Capacitance	Ca,b	Between A and B, DE = GND, f = 2MHz			12		рF

### DC ELECTRICAL CHARACTERISTICS (continued)

(V<sub>CC</sub> = +3.0V to +3.6V, T<sub>A</sub> = -40°C to +125°C, unless otherwise noted. Typical values are at V<sub>CC</sub> = +3.3V and T<sub>A</sub> = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Receiver Differential Threshold	VTHF	$-7V \le V_{CM} \le 12V$ , V <sub>OD</sub> falling	-200		-10	mV
Voltage (MAX14840E Only)	VTHR	$-7V \le V_{CM} \le 12V$ , V <sub>OD</sub> rising	10		200	mV
Receiver Input Hysteresis (MAX14840E Only)		VCM = 0V		170		mV
Receiver Differential Threshold Voltage (MAX14841E Only)			-200	-105	-10	mV
Receiver Input Hysteresis (MAX14841E Only)	Δντη	VCM = 0V		10		mV
LOGIC INTERFACE						
Input High Voltage		DE, DI	2.0		5.5	V
Input High Voltage	VIH	RE	2.0			
Input Low Voltage	VIL	DE, DI, RE			0.8	V
Input Hysteresis	VHYS	DE, DI, RE		50		mV
Input Current	lin	DE, DI, RE	-1		+1	μA
Input Impedance on First Transition		DE, RE	1		10	kΩ
Output High Voltage	Voh	$\overline{\text{RE}}$ = GND, I <sub>O</sub> = -1mA, V <sub>A</sub> - V <sub>B</sub> > 200mV	V <sub>CC</sub> - 1.5			V
Output Low Voltage	Vol	$\overline{\text{RE}}$ = GND, I <sub>O</sub> = 1mA, V <sub>A</sub> - V <sub>B</sub> < -200mV			0.4	V
Three-State Output Current at Receiver	Iozr	$\overline{\text{RE}}$ = V <sub>CC</sub> , 0V $\leq$ V <sub>O</sub> $\leq$ V <sub>CC</sub>	-1		+1	μΑ
Receiver Output Short-Circuit Current	IOSR	$0V \le V_{RO} \le V_{CC}$	-95		+95	mA
PROTECTION						
Thermal Shutdown Threshold	T <sub>TS</sub>			160		°C
Thermal Shutdown Hysteresis	TTSH			15		°C
		IEC 61000-4-2 Air Gap Discharge	±20 ±12			
ESD Protection: A, B to GND		IEC 61000-4-2 Contact Discharge			kV	
		HBM		±35		
ESD Protection: All Other Pins		НВМ		±2		kV

### SWITCHING CHARACTERISTICS

 $(V_{CC} = +3.0V \text{ to } +3.6V, T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{CC} = +3.3V \text{ and } T_A = +25^{\circ}\text{C}.)$  (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
DRIVER						
Propagation Dolay	t <sub>DPLH</sub>	$R_L = 54\Omega$ , $C_L = 50pF$ , Figures 2 and 3	5	12	20	00
Propagation Delay	<b>t</b> DPHL	PHL (Note 5)		12	20	ns
Differential Driver Output Skew ltDPLH - tDPHLI	<b>t</b> DSKEW	$R_L = 54\Omega$ , $C_L = 50pF$ , Figures 2 and 3 (Notes 5, 8)			2	ns
Driver Differential Output Rise or Fall Time	t <sub>HL</sub> , t <sub>LH</sub>	$R_L = 54\Omega$ , $C_L = 50pF$ , Figures 2 and 3 (Notes 5, 8)			7.5	ns

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### SWITCHING CHARACTERISTICS (continued)

(VCC = +3.0V to +3.6V, TA = -40°C to +125°C, unless otherwise noted. Typical values are at VCC = +3.3V and TA = +25°C.) (Notes 2, 3)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS	
Maximum Data Rate	DRMAX		40			Mbps	
Driver Enable to Output High	tdzh	$R_L = 110\Omega$ , $C_L = 50pF$ , Figures 4 and 5 (Notes 5, 6)			30	ns	
Driver Enable to Output Low	tDZL	$R_L = 110\Omega$ , $C_L = 50pF$ , Figures 4 and 5 (Notes 5, 6)			30	ns	
Driver Disable Time from Low	tDLZ	$R_L = 110\Omega$ , $C_L = 50pF$ , Figures 4 and 5 (Notes 5, 6)			30	ns	
Driver Disable Time from High	tDHZ	$R_L = 110\Omega$ , $C_L = 50pF$ , Figures 4 and 5 (Notes 5, 6)			30	ns	
Driver Enable from Shutdown to Output Low	tDZL(SHDN)	$R_L = 110\Omega$ , $C_L = 50pF$ , Figures 4 and 5 (Notes 5, 6)			4	μs	
Driver Enable from Shutdown to Output High	tDZH(SHDN)	$R_L = 110\Omega$ , $C_L = 50pF$ , Figures 4 and 5 (Notes 5, 6)			4	μs	
Time to Shutdown	<b>t</b> SHDN	(Note 7)	50		800	ns	
RECEIVER							
Propagation Delay	tRPLH	$-C_L = 15pF$ , Figures 6 and 7 (Note 5)			25	ne	
Topagation Delay	t <sub>RPHL</sub>	tRPHL			25	- ns	
Receiver Output Skew	<b>t</b> RSKEW	C <sub>L</sub> = 15pF, Figures 6 and 7 (Notes 5, 8)			2	ns	
Maximum Data Rate	DRMAX		40			Mbps	
Receiver Enable to Output High	trzh	$R_L = 1k\Omega$ , $C_L = 15pF$ , Figure 8 (Notes 5, 6)			20	ns	
Receiver Enable to Output Low	t <sub>RZL</sub>	$R_L = 1k\Omega$ , $C_L = 15pF$ , Figure 8 (Notes 5, 6)			20	ns	
Receiver Disable Time from Low	t <sub>RLZ</sub>	$R_L = 1k\Omega$ , $C_L = 15pF$ , Figure 8 (Notes 5, 6)			20	ns	
Receiver Disable Time from High	trhz	$R_L = 1k\Omega$ , $C_L = 15pF$ , Figure 8 (Notes 5, 6)			20	ns	
Receiver Enable from Shutdown to Output Low	tRZL(SHDN)	$R_L = 1k\Omega$ , $C_L = 15pF$ , Figure 8 (Notes 5, 6)			4	μs	
Receiver Enable from Shutdown to Output High	<sup>t</sup> RZH(SHDN)	$R_L = 1k\Omega$ , $C_L = 15pF$ , Figure 8 (Notes 5, 6)			4	μs	
Time to Shutdown	tSHDN	(Note 7)	50		800	ns	

**Note 2:** All devices are 100% production tested at  $T_A = +25^{\circ}C$ . Specifications for all temperature limits are guaranteed by design.

Note 3: All currents into the device are positive; all currents out of the device are negative. All voltages are referenced to device ground, unless otherwise noted.

Note 4: ΔVOD and ΔVOC are the changes in VOD and VOC, respectively, when the DI input changes state.

Note 5: Capacitive load includes test probe and fixture capacitance.

Note 6: The timing parameter refers to the driver or receiver enable delay when the device has exited the initial hot-swap protect state and is in normal operating mode.

Note 7: Shutdown is enabled by driving RE high and DE low. The device is guaranteed to have entered shutdown after tSHDN has elapsed.

Note 8: Parameter is guaranteed by characterization and not production tested.

### **Test and Timing Diagrams**





Figure 1. Driver DC Test Load

Figure 2. Driver Timing Test Circuit



Figure 3. Driver Propagation Delays



Figure 4. Driver Enable and Disable Times (tDZH, tDHZ)



### **Test and Timing Diagrams (continued)**

Figure 5. Driver Enable and Disable Times (tDLZ, tDZL)



Figure 6. Receiver Propagation Delay Test Circuit



Figure 7. Receiver Propagation Delays

## Test and Timing Diagrams (continued)



Figure 8. Receiver Enable and Disable Times

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**MAX14840E/MAX14841E** 





FREQUENCY (kHz)

**Pin Configurations** TOP VIEW GND Vcc В А 7 6 5 8 R0 1 8 Vcc ΜΛΧΙ/Μ RE 2 MIXIM 7 B MAX14840E MAX14840E MAX14841E MAX14841E DE 3 6 A 5 GND DI 4 \*EP + SO 2 3 4 1 RE DE RO DI TDFN \*CONNECT EXPOSED PAD (EP) TO GND.

### Pin Descriptions

PIN	NAME	FUNCTION
1	RO	Receiver Output. See the Function Table.
2	RE	Active-Low Receiver-Output Enable. Drive $\overline{RE}$ low to enable RO. RO is high impedance when $\overline{RE}$ is high. Drive $\overline{RE}$ high and DE low to enter low-power shutdown mode. $\overline{RE}$ is a hot-swap input (see the <i>Hot-Swap Capability</i> section for details).
3	DE	Driver-Output Enable. Drive DE high to enable driver outputs. These outputs are high impedance when DE is low. Drive RE high and DE low to enter low-power shutdown mode. DE is a hot-swap input (see the <i>Hot-Swap Capability</i> section for details).
4	DI	Driver Input. With DE high, a low on DI forces the A output low and the B output high. Similarly, a high on DI forces the A output high and the B output low.
5	GND	Ground
6	A	Noninverting Receiver Input and Noninverting Driver Output
7	В	Inverting Receiver Input and Inverting Driver Output
8	Vcc	Positive Supply Voltage Input. Bypass V <sub>CC</sub> with a 0.1µF ceramic capacitor to GND.
_	EP	Exposed Pad (TDFN Only). Connect EP to GND.

## \_Function Table

		TRANSMITTING				
	INPUTS		OUTI	PUTS		
RE	DE	DI	В	А		
Х	1	1	0	1		
Х	1	0	1	0		
0	0	Х	High Impedance	High Impedance		
1	0	Х	Shutdown	(see note)		
		RECEIVING (MAX14840E	Ξ)			
	INPUTS		OUTI	PUTS		
RE	DE	A-B	R	0		
0	Х	≥ 200mV		1		
0	Х	≤ -200mV	(	)		
0	Х	Open/Shorted	Previous State			
1	1	Х	High Im	bedance		
1	0	Х	Shutdown	(see note)		
		RECEIVING (MAX14841E	Ξ)			
	INPUTS		OUTI	PUTS		
RE	DE	A-B	RO			
0	Х	≥ -10mV	1			
0	Х	≤ -200mV	0			
0	Х	Open/Shorted		1		
1	1	Х	High Im	oedance		
1	0	Х	Shutdown (see note)			

X = Don't care.

*Note:* Shutdown mode, driver, and receiver outputs are in high impedance.

### Functional Diagram



### \_Detailed Description

The MAX14840E/MAX14841E are +3.3V ESD-protected RS-485 transceivers intended for high-speed, half-duplex communications. A hot-swap capability eliminates false transitions on the bus during power-up or hot insertion.

The MAX14840E features symmetrical fail-safe and larger receiver hysteresis, providing improved noise rejection and improved recovered signals in high-speed and long cable applications. The MAX14841E has true failsafe receiver inputs guaranteeing a logic-high receiver output when inputs are shorted or open. All devices have a 1-unit load receiver input impedance, allowing up to 32 transceivers on the bus.

The MAX14840E/MAX14841E transceivers draw 1.5mA (typ) supply current when unloaded or when fully loaded with the drivers disabled.

#### Symmetrical Fail Safe (MAX14840E)

At high data rates and with long cable lengths, the signal at the end of the cable is attenuated and distorted due to the lowpass characteristic of the transmission line. Under these conditions, fail-safe RS-485 receivers, which have offset threshold voltages, produce recovered signals with uneven mark-space ratios. The MAX14840E has symmetrical receiver thresholds, as shown in Figure 9. This produces near even mark-space ratios at the receiver's output (RO). The MAX14840E also has higher receiver hysteresis than the MAX14841E and most other RS-485 transceivers. This results in higher receiver noise tolerance.

Symmetrical fail safe means that the receiver's output (RO) remains at the same logic state that it was before the differential input voltage VOD went to OV. Under

normal conditions, where UART signaling is used, this means that the state on the line prior to all drivers being disabled is a logic-high (i.e., a UART STOP bit).

#### True Fail Safe (MAX14841E)

The MAX14841E guarantees a logic-high receiver output when the receiver inputs are shorted or open or when they are connected to a terminated transmission line with all drivers disabled. This is the case if the receiver input threshold is between -10mV and -200mV. RO is logic-high if the differential receiver input voltage V<sub>OD</sub> is greater than or equal to -10mV.

#### Hot-Swap Capability Hot-Swap Inputs

When circuit boards are inserted into a hot or powered backplane, disturbances to the enable inputs and differential receiver inputs can lead to data errors. Upon initial circuit board insertion, the processor undergoes its powerup sequence. During this period, the processor output drivers are high impedance and are unable to drive the DE and  $\overline{RE}$  inputs of the MAX14840E/MAX14841E to a defined logic level. Leakage currents up to 10µA from the high-impedance output of a controller could cause DE and  $\overline{RE}$  to drift to an incorrect logic state. Additionally, parasitic circuit board capacitance could cause coupling of VCC or GND to DE and  $\overline{RE}$ . These factors could improperly enable the driver or receiver. However, the MAX14840E/MAX14841E have hot-swap inputs that avoid these potential problems.

When V<sub>CC</sub> rises, an internal pulldown circuit holds DE low and  $\overline{\text{RE}}$  high. After the initial power-up sequence, the pulldown circuit becomes transparent, resetting the hot-swap-tolerable inputs.



Figure 9. Symmetrical Hysteresis

#### How-Swap Input Circuitry

The MAX14840E/MAX14841E DE and RE enable inputs feature hot-swap capability. At the input, there are two nMOS devices, M1 and M2 (Figure 10). When VCC ramps from OV, an internal 15µs timer turns on M2 and sets the SR latch that also turns on M1. Transistors M2 (a 1mA current sink) and M1 (a 100uA current sink) pull DE to GND through a 5.6k $\Omega$  resistor. M2 is designed to pull DE to the disabled state against an external parasitic capacitance up to 100pF that can drive DE high. After 15µs, the timer deactivates M2 while M1 remains on, holding DE low against three-state leakages that can drive DE high. M1 remains on until an external source overcomes the required input current. At this time, the SR latch resets and M1 turns off. When M1 turns off, DE reverts to a standard, high-impedance CMOS input. Whenever V<sub>CC</sub> drops below 1V, the hot-swap input is reset.

For  $\overline{\text{RE}}$ , there is a complementary circuit employing two pMOS devices pulling  $\overline{\text{RE}}$  to V<sub>CC</sub>.

### ±35kV ESD Protection

ESD protection structures are incorporated on all pins to protect against electrostatic discharges encountered during handling and assembly. The driver outputs and receiver inputs of the MAX14840E family of devices have extra protection against static electricity. The ESD structures withstand high ESD in all states: normal operation, shutdown, and powered down. After an ESD event, the MAX14840E/MAX14841E keep working without latchup or damage.

ESD protection can be tested in various ways. The transmitter outputs and receiver inputs of the MAX14840E/ MAX14841E are characterized for protection to the following limits:

- ±35kV HBM
- ±20kV using the Air Gap Discharge method specified in IEC 61000-4-2
- ±12kV using the Contact Discharge method specified in IEC 61000-4-2



Figure 10. Simplified Structure of the Driver Enable Pin (DE)

#### **ESD Test Conditions**

ESD performance depends on a variety of conditions. Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

#### Human Body Model

Figure 11 shows the HBM, and Figure 12 shows the current waveform it generates when discharged into a low-impedance state. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the test device through a  $1.5k\Omega$  resistor.

#### IEC 61000-4-2

The IEC 61000-4-2 standard covers ESD testing and performance of finished equipment. However, it does not specifically refer to integrated circuits. The MAX14840E/MAX14841E family of devices helps you design equipment to meet IEC 61000-4-2, without the need for additional ESD protection components.



Figure 11. Human Body ESD Test Model



Figure 12. Human Body current Waveform

The major difference between tests done using the HBM and IEC 61000-4-2 is higher peak current in IEC 61000-4-2 because series resistance is lower in the IEC 61000-4-2 model. Hence, the ESD withstand voltage measured to IEC 61000-4-2 is generally lower than that measured using the HBM.

Figure 13 shows the IEC 61000-4-2 model, and Figure 14 shows the current waveform for IEC 61000-4-2 ESD Contact Discharge test.

### Applications Information

#### High-Speed Operation

The MAX14840E and MAX14841E are high-performance RS-485 transceivers supporting data rates up to 40Mbps.

#### **Driver Output Protection**

Two mechanisms prevent excessive output current and power dissipation caused by faults or by bus contention. Current limit on the output stage provides



Figure 13. IEC 61000-4-2 ESD Test Model



Figure 14. IEC 61000-4-2 ESD Generator Current Waveform



Figure 15. Typical Half-Duplex RS-485 Network

immediate protection against short circuits over the whole common-mode voltage range (see the *Typical Operating Characteristics*). Additionally, a thermal shutdown circuit forces the driver outputs into a high-impedance state if the die temperature exceeds +160°C (typ).

#### Low-Power Shutdown Mode

Low-power shutdown mode is initiated by bringing  $\overline{RE}$  high and DE low. In shutdown, the devices draw less than 10µA of supply current.

RE and DE can be driven simultaneously; the parts are guaranteed not to enter shutdown if RE is high and DE is low for less than 50ns. If the inputs are in this state for at least 800ns, the parts are guaranteed to enter shutdown.

#### **Typical Applications**

The MAX14840E/MAX14841E transceivers are designed for bidirectional data communications on multipoint bus transmission lines. Figure 15 shows a typical network application circuit. To minimize reflections, terminate the line at both ends with its characteristic impedance and keep stub lengths off the main line as short as possible.

### **Chip Information**

PROCESS: BICMOS

#### **Package Information**

For the latest package outline information and land patterns, go to <u>www.maxim-ic.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
8 SO	S8+4	<u>21-0041</u>
8 TDFN-EP	T833+2	<u>21-0137</u>

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